

Three Phase Full Controlled Bridges

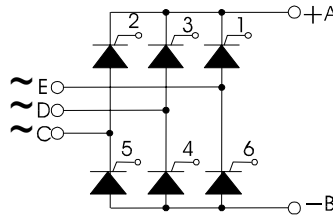
PSDT 110

$I_{dAV} = 110A$
 $V_{RRM} = 400-1600 V$

Preliminary Data Sheet

V_{RSM} V_{DSM}	V_{RRM} V_{DRM}	Type
500	400	PSDT 110/04
900	800	PSDT 110/08
1300	1200	PSDT 110/12
1500	1400	PSDT 110/14
*1700	*1600	PSDT 110/16

* Delivery on request



Symbol	Test Conditions	Maximum Ratings
I_{dAV}	$T_C = 85^\circ C$ per module	110 A
I_{TSM}	$T_{VJ} = 45^\circ C$ $t = 10 \text{ ms}$ (50 Hz), sine	1150 A
	$V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	1230 A
	$T_{VJ} = T_{VJM}$ $t = 10 \text{ ms}$ (50 Hz), sine	1000 A
	$V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	1070 A
$\int i^2 dt$	$T_{VJ} = 45^\circ C$ $t = 10 \text{ ms}$ (50 Hz), sine	6600 $A^2 s$
	$V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	6280 $A^2 s$
	$T_{VJ} = T_{VJM}$ $t = 10 \text{ ms}$ (50 Hz), sine	5000 $A^2 s$
	$V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	4750 $A^2 s$
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ repetitive, $I_T = 50 A$	150 $A/\mu s$
	$f = 400 \text{ Hz}$, $t_p = 200 \mu s$ $V_D = 2/3 V_{DRM}$	
	$I_G = 0.3 A$ non repetitive, $I_T = 1/3 \cdot I_{dAV}$	500 $A/\mu s$
	$di_G/dt = 0.3 A/\mu s$	
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$ $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$, method 1 (linear voltage rise)	1000 $V/\mu s$
P_{GM}	$T_{VJ} = T_{VJM}$ $t_p = 30 \mu s$	$\leq 10 W$
	$I_T = I_{TAVM}$ $t_p = 500 \mu s$	$\leq 5 W$
P_{GAVM}		$\leq 0.5 W$
V_{RGM}		10 V
T_{VJ}		-40 ... + 125 $^\circ C$
T_{VJM}		125 $^\circ C$
T_{stg}		-40 ... + 125 $^\circ C$
V_{ISOL}	50/60 HZ, RMS $t = 1 \text{ min}$	2500 V ~
	$I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$	3000 V ~
M_d	Mounting torque (M6)	5 Nm
	Terminal connection torque (M6)	5 Nm
Weight	typ.	270 g

Features

- Package with screw terminals
- Isolation voltage 3000 V~
- Planar glasspassivated chips
- Low forward voltage drop
- UL registered, E 148688

Applications

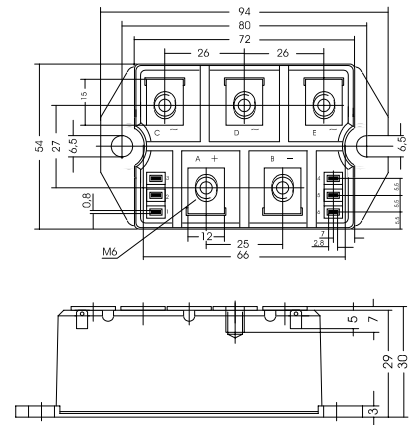
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Motor control
- Power converter

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- High power density

Package, style and outline

Dimensions in mm (1mm = 0.0394")



Symbol	Test Conditions	Characteristic Value	
I_D, I_R	$T_{VJ} = T_{VJM}, V_R = V_{RRM}, V_D = V_{DRM}$	≤ 5 mA	
V_T	$I_T = 200A, T_{VJ} = 25^\circ C$	≤ 1.75 V	
V_{TO}	For power-loss calculations only ($T_{VJ} = T_{VJM}$)	0.85 V	
r_T		6 m Ω	
V_{GT}	$V_D = 6V$	$T_{VJ} = 25^\circ C$	≤ 1.5 V
		$T_{VJ} = -40^\circ C$	≤ 1.6 V
I_{GT}	$V_D = 6V$	$T_{VJ} = 25^\circ C$	≤ 100 mA
		$T_{VJ} = -40^\circ C$	≤ 200 mA
V_{GD}	$T_{VJ} = T_{VJM}, V_D = 2/3 V_{DRM}$	≤ 0.2 V	
I_{GD}	$T_{VJ} = T_{VJM}, V_D = 2/3 V_{DRM}$	≤ 5 mA	
I_L	$T_{VJ} = 25^\circ C, t_p = 30\mu s$	≤ 450 mA	
	$I_G = 0.3A, di_G/dt = 0.3A/\mu s$		
I_H	$T_{VJ} = 25^\circ C, V_D = 6V, R_{GK} = \infty$	≤ 200 mA	
t_{gd}	$T_{VJ} = 25^\circ C, V_D = 1/2 V_{DRM}$	≤ 2 μs	
	$I_G = 0.3A, di_G/dt = 0.3A/\mu s$		
t_q	$T_{VJ} = T_{VJM}, I_T = 20A, t_p = 200\mu s, V_R = 100V$	150 μs	
	$-di/dt = 10A/\mu s, dv/dt = 15V/\mu s, V_D = 2/3 V_{DRM}$		
R_{thJC}	per thyristor; sine 180°el	0.65 K/W	
	per module	0.108 K/W	
R_{thJK}	per thyristor; sine 180° el	0.8 K/W	
	per module	0.133 K/W	
d_s	Creeping distance on surface	10.0 mm	
d_A	Creeping distance in air	9.4 mm	
a	Max. allowable acceleration	50 m/s ²	

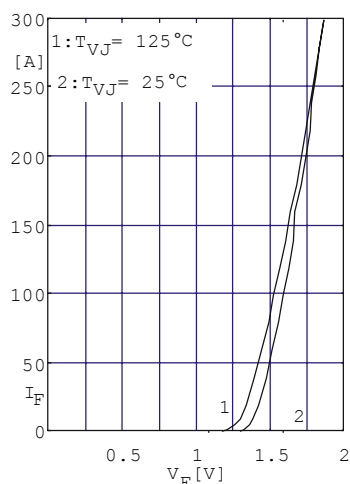


Fig. 1 Forward current vs. voltage drop per diode or thyristor

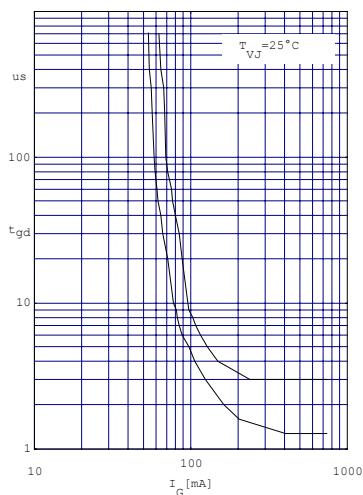


Fig. 2 Gate trigger delay time

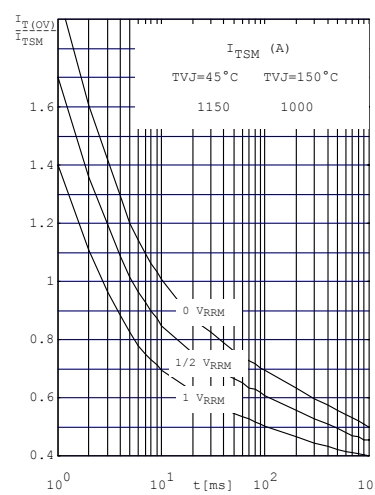


Fig. 3 Surge overload current per diode (or thyristor) I_{FSM} , I_{TSM} : Crest value t : duration

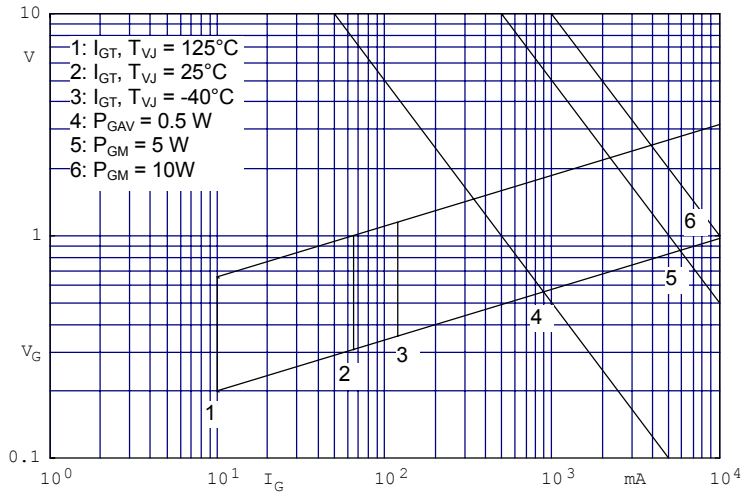


Fig.4 Gate trigger characteristic

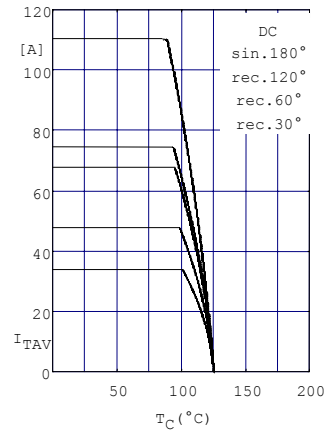


Fig.5 Maximum forward current at case temperature

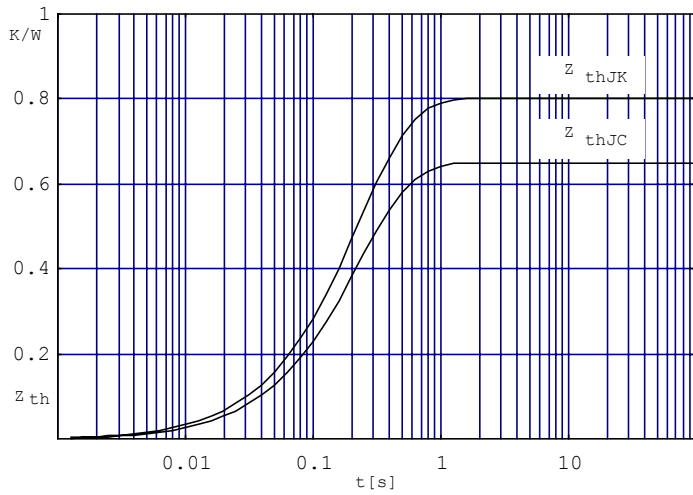


Fig.6 Transient thermal impedance per thyristor or diode (calculated)

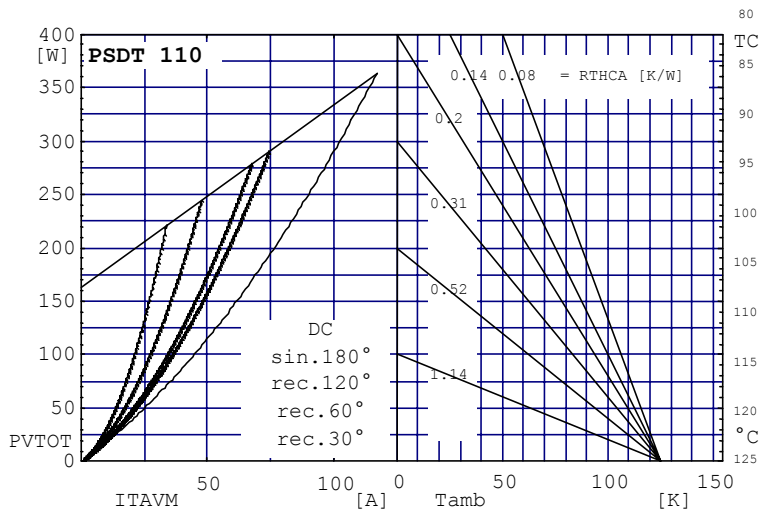


Fig. 7 Power dissipation vs. direct output current and ambient temperature